



DMT10H4M5LPS

100V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C (Note 9)
100V	4.3mΩ @ V _{GS} = 10V	100A

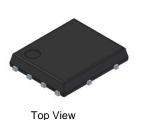
Description

This new generation N-Channel Enhancement Mode MOSFET is designed to minimize $R_{DS(ON)}$, yet maintain superior switching performance. This device is ideal for use in notebook battery power management and load switch.

Applications

- Motor Control
- DC-DC Converters
- Power Management

PowerDI5060-8 (Standard)



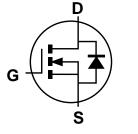
Bottom View



- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low R_{DS(ON)} Minimizes On-State Losses
- Low Input Capacitance
- Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

- Case: PowerDI[®]5060-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.097 grams (Approximate)



Internal Schematic

s [] D s [] D s [] D g [] D g [] D Top View Pin Configuration

Ordering Information (Note 4)

Part Number	Case	Packaging
DMT10H4M5LPS-13	PowerDI5060-8 (Standard)	2,500/Tape & Reel

Pin1

EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
 See http://www.diodes.com/quality/lead_free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website athttps://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

Notes:



);; = Manufacturer's Marking 10H4M5LS = Product Type Marking Code YYWW = Date Code Marking YY or \underline{YY} = Last Two Digits of Year (ex: 19 = 2019) WW or \underline{WY} = Week Code (01 to 53)



Maximum Ratings ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V _{DSS}	100	V		
Gate-Source Voltage			V _{GSS}	±20	V
	Steady	T _A = +25°C	- I _D -	19	•
Continuous Drain Current, V _{GS} = 10V (Note 5)	State	T _A = +70°C		15	A
	Steady State	T _C = +25°C	ID	100	
Continuous Drain Current, $V_{GS} = 10V$ (Note 6)		$T_C = +70^{\circ}C$		100	A
		(Note 9)			
Pulsed Drain Current (10µs Pulse, T _C =+25°C, Package Lir		I _{DM}	400	A	
Maximum Continuous Body Diode Forward Current (Note	Is	100	A		
Pulsed Body Diode Forward Current (10µs Pulse, Tc=+25°C, Package Limited)			I _{SM}	400	A
Avalanche Current (Note 7) L=0.3mH			I _{AS}	40	A
Avalanche Energy (Note 7) L=0.3mH			EAS	240	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	$T_A = +25^{\circ}C$	PD	2.3	W
Thermal Resistance, Junction to Ambient (Note 5)		R _{0JA}	54	°C/W
Total Power Dissipation (Note 6)	$T_{C} = +25^{\circ}C$	PD	113	W
Thermal Resistance, Junction to Case (Note 6)		R _{θJC}	1.1	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

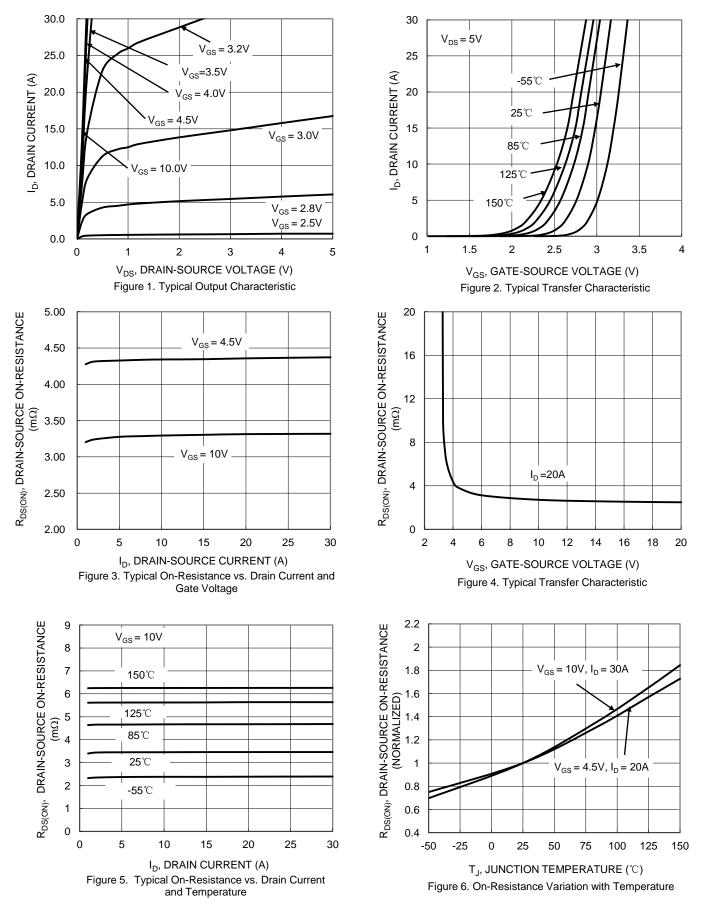
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Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	100	_	_	V	$V_{GS} = 0V, I_{D} = 10mA$	
Zero Gate Voltage Drain Current	I _{DSS}		_	1	μA	$V_{DS} = 80V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}		_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	1.3	_	2.5	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance		-	3.5	4.3	mΩ	$V_{GS} = 10V, I_D = 30A$	
	R _{DS(ON)}		4.7	6.2	11122	$V_{GS} = 4.5V, I_D = 20A$	
Diode Forward Voltage	V _{SD}	_	—	1.2	V	$V_{GS} = 0V, I_{S} = 30A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss	_	4843		pF	$V_{DS} = 50V, V_{GS} = 0V$ f = 1MHz	
Output Capacitance	Coss	_	1302	_			
Reverse Transfer Capacitance	C _{rss}	_	25.5	_			
Gate Resistance	Rg		2.1	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge	Qg	_	80	_			
Gate-Source Charge	Q _{gs}	_	14	_	nC	$V_{DD} = 50V, I_D = 30A,$ $V_{GS} = 10V$	
Gate-Drain Charge	Q _{gd}	_	18	_			
Turn-On Delay Time	t _{D(ON)}	_	9	_		$V_{DD} = 50V, V_{GS} = 10V,$ $I_D = 30A, R_g = 4.7\Omega, R_L=1.1\Omega$	
Turn-On Rise Time	t _R	_	26	_	ns		
Turn-Off Delay Time	t _{D(OFF)}	—	76	_			
Turn-Off Fall Time	tF	_	50				
Reverse Recovery Time	t _{RR}	_	63		ns	$I_{-} = 22.54$ di/dt = 1004/up	
Reverse Recovery Charge	Q _{RR}	_	133		nC	I _F = 22.5A, di/dt = 100A/μs	

Notes: 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.

Device mounted on PK-4 PC board, with minimum recommended bad ayout, si
 Thermal resistance from junction to soldering point (on the exposed drain pad).
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.
 Package limited.



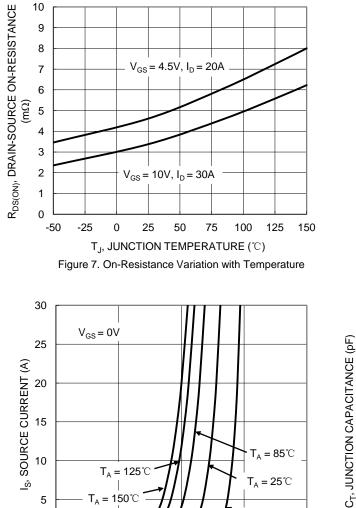
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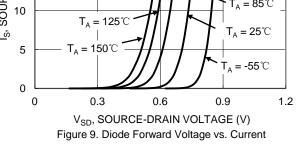


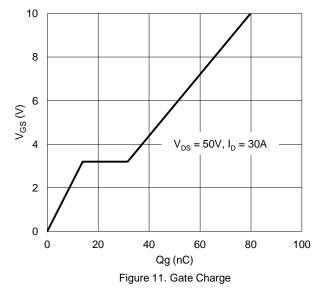
DMT10H4M5LPS Document number: DS41337 Rev. 3 - 2

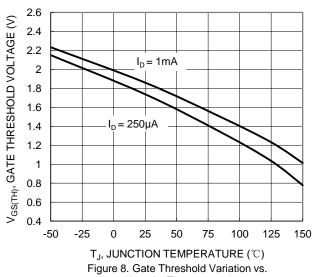


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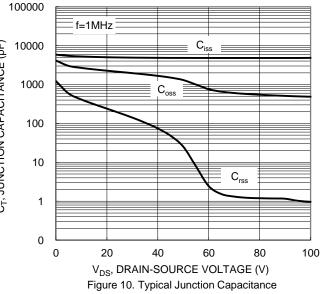








JunctionTemperature



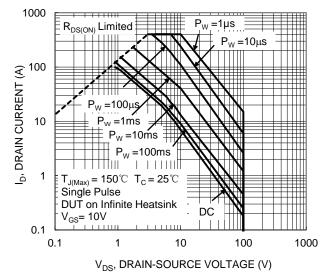
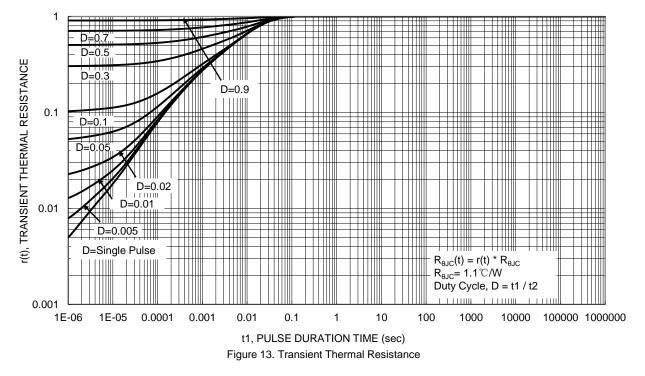


Figure 12. SOA, Safe Operation Area

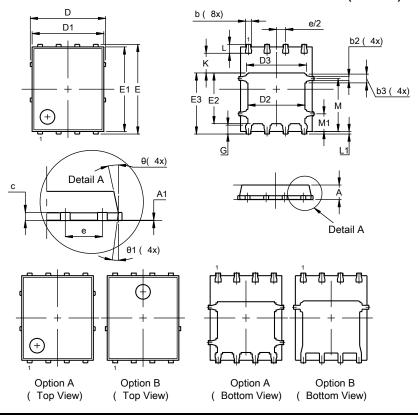






Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

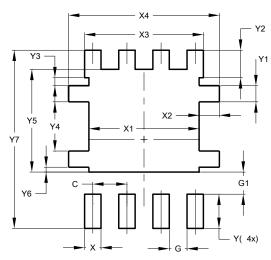


PowerDI5060-8 (Standard)

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Dim	Min	Max	Тур		
Α	0.90	1.20			
A1	0.00	0.05	-		
b	0.33	0.51			
b2	0.200	0.350			
b3	0.40	0.80	0.60		
C	0.230	0.354			
D (Option A)	5.	15 BSC			
D (Option B)		30 BSC			
D1	4.70	5.40			
D2	3.70	4.25			
D3	3.90	4.70			
E	6.	15 BSC			
E1	5.60	6.06			
E2	3.28	3.92			
E3	3.99	4.39			
e	1.27 BSC				
G	0.40	0.71			
к	0.51	1.45	-		
L	0.38	0.71			
L1	0.100	0.200			
М	3.235	4.035			
M1	1.00	1.40	1.21		
θ	8º	12º			
θ1	6°	8º	7°		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



PowerDI5060-8 (Standard)

Dimensions	Value (in mm)
С	1.270
G	0.660
G1	0.820
Х	0.610
X1	4.300
X2	0.755
Х3	4.420
X4	5.610
Y	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	4.100
Y6	0.180
Y7	6.610



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